



P-Channel 30 V (D-S) MOSFET with Schottky Diode

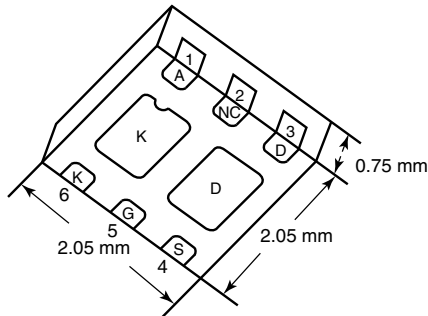
PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω) Max.	I_D (A)	Q_g (Typ.)
- 30	0.065 at $V_{GS} = -10$ V	- 4.5 ^a	6.6 nC
	0.080 at $V_{GS} = -4.5$ V	- 4.5 ^a	
	0.092 at $V_{GS} = -3.7$ V	- 4.5 ^a	
	0.125 at $V_{GS} = -2.5$ V	- 3	

SCHOTTKY PRODUCT SUMMARY

V_{KA} (V)	V_f (V) Diode Forward Voltage	I_F (A) ^a
30	0.56 at 1 A	2

PowerPAK SC-70-6 Dual



Ordering Information:

SiA817EDJ-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

- LITTLE FOOT® Plus Schottky Power MOSFET
- Thermally Enhanced PowerPAK® SC-70 Package
 - Small Footprint Area
 - Low On-Resistance
 - Thin 0.75 mm Profile
- Typical ESD Protection (MOSFET): 1500 V (HBM)
- 100 % R_g Tested
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

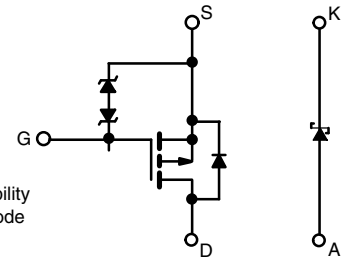
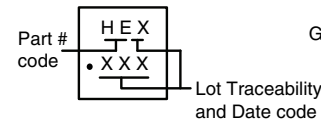


RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Portable Devices such as Smart Phones, Tablet PCs and Mobile Computing
 - Battery Charger Switch
 - Buck Converter
 - Power Management

Marking Code



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage (MOSFET)	V_{DS}	- 30	V
Reverse Voltage (Schottky)	V_{KA}	30	
Gate-Source Voltage (MOSFET)	V_{GS}	± 12	
Continuous Drain Current ($T_J = 150^\circ\text{C}$) (MOSFET)	I_D	$T_C = 25^\circ\text{C}$	- 4.5 ^a
		$T_C = 70^\circ\text{C}$	- 4.5 ^a
		$T_A = 25^\circ\text{C}$	- 4.2 ^{b, c}
		$T_A = 70^\circ\text{C}$	- 3.4 ^{b, c}
Pulsed Drain Current (MOSFET) ($t = 300 \mu\text{s}$)	I_{DM}	- 15	A
Continuous Source-Drain Diode Current (MOSFET Diode Conduction)	I_S	$T_C = 25^\circ\text{C}$	- 4.5 ^a
		$T_A = 25^\circ\text{C}$	- 1.6 ^{b, c}
Average Forward Current (Schottky)	I_F	2 ^b	W
Pulsed Forward Current (Schottky)	I_{FM}	3	
Maximum Power Dissipation (MOSFET)	P_D	$T_C = 25^\circ\text{C}$	6.5
		$T_C = 70^\circ\text{C}$	5
		$T_A = 25^\circ\text{C}$	1.9 ^{b, c}
		$T_A = 70^\circ\text{C}$	1.2 ^{b, c}
Maximum Power Dissipation (Schottky)	P_D	$T_C = 25^\circ\text{C}$	6.8
		$T_C = 70^\circ\text{C}$	4.3
		$T_A = 25^\circ\text{C}$	1.6 ^{b, c}
		$T_A = 70^\circ\text{C}$	1 ^{b, c}
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	$^\circ\text{C}$
Soldering Recommendations (Peak Temperature) ^{d, e}		260	

SiA817EDJ

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THERMAL RESISTANCE RATINGS

Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient (MOSFET) ^{b, f}	$t \leq 5$ s	R_{thJA}	52	65	°C/W
Maximum Junction-to-Case (Drain) (MOSFET)	Steady State	R_{thJC}	12.5	16	
Maximum Junction-to-Ambient (Schottky) ^{b, f}	$t \leq 5$ s	R_{thJA}	62	76	
Maximum Junction-to-Case (Drain) (Schottky)	Steady State	R_{thJC}	15	18.5	

Notes:

a. Package limited.

b. Surface mounted on 1" x 1" FR4 board.

c. $t = 10$ s.d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

f. Maximum under steady state conditions is 110 °C/W.

SPECIFICATIONS ($T_J = 25$ °C, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = - 250 μA	- 30			V	
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = - 250 μA		- 23		mV/°C	
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			2.7			
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	- 0.6		- 1.3	V	
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 4.5 V			± 0.5	μA	
		V _{DS} = 0 V, V _{GS} = ± 12 V			± 10		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 30 V, V _{GS} = 0 V			- 1		
		V _{DS} = - 30 V, V _{GS} = 0 V, T _J = 55 °C			- 10		
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≤ 5 V, V _{GS} = - 10 V	- 8			A	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V, I _D = - 3 A		0.054	0.065	Ω	
		V _{GS} = - 4.5 V, I _D = - 2 A		0.065	0.080		
		V _{GS} = - 3.7 V, I _D = - 1 A		0.070	0.092		
		V _{GS} = - 2.5 V, I _D = - 1 A		0.095	0.125		
Forward Transconductance ^a	g _{fs}	V _{DS} = - 10 V, I _D = - 3 A		9		S	
Dynamic ^b							
Input Capacitance	C _{iss}	V _{DS} = - 15 V, V _{GS} = 0 V, f = 1 MHz		600		pF	
Output Capacitance	C _{oss}			55			
Reverse Transfer Capacitance	C _{rss}			50			
Total Gate Charge	Q _g	V _{DS} = - 15 V, V _{GS} = - 10 V, I _D = - 4.2 A		14	23	nC	
Gate-Source Charge	Q _{gs}	V _{DS} = - 15 V, V _{GS} = - 4.5 V, I _D = - 4.2 A		6.6	10		
Gate-Drain Charge	Q _{gd}			1.3			
Gate Resistance	R _g			2			
Turn-On Delay Time	t _{d(on)}	f = 1 MHz	1.1	5.5	11	Ω	
Rise Time	t _r		V _{DD} = - 15 V, R _L = 4.4 Ω I _D ≅ - 3.4 A, V _{GEN} = - 4.5 V, R _g = 1 Ω		20	40	ns
Turn-Off DelayTime	t _{d(off)}				20	40	
Fall Time	t _f				23	45	
Turn-On Delay Time	t _{d(on)}			10	20		
Rise Time	t _r	V _{DD} = - 15 V, R _L = 4.4 Ω I _D ≅ - 3.4 A, V _{GEN} = - 10 V, R _g = 1 Ω		10	20		
Turn-Off DelayTime	t _{d(off)}			10	20		
Fall Time	t _f			25	50		
				7	15		
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			- 4.5	A	
Pulse Diode Forward Current	I _{SM}				- 15		
Body Diode Voltage	V _{SD}	I _S = - 3.4 A, V _{GS} = 0 V		- 0.9	- 1.2	V	
Body Diode Reverse Recovery Time	t _{rr}	I _F = - 3.4 A, dI/dt = 100 A/μs, T _J = 25 °C		16	30	ns	
Body Diode Reverse Recovery Charge	Q _{rr}			8	15	nC	
Reverse Recovery Fall Time	t _a			9		ns	
Reverse Recovery Rise Time	t _b			7			

Notes:

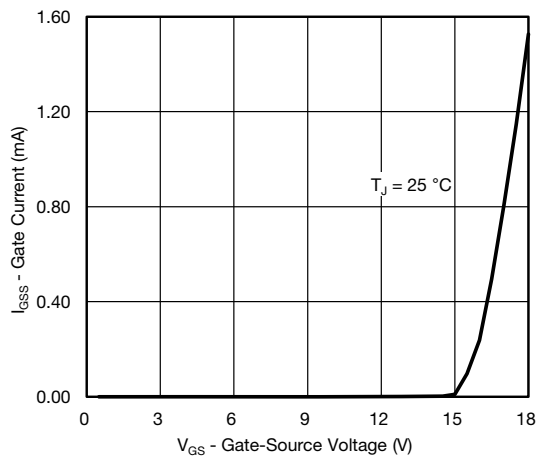
a. Pulse test; pulse width ≤ 300 μ s, duty cycle ≤ 2 %.

b. Guaranteed by design, not subject to production testing.

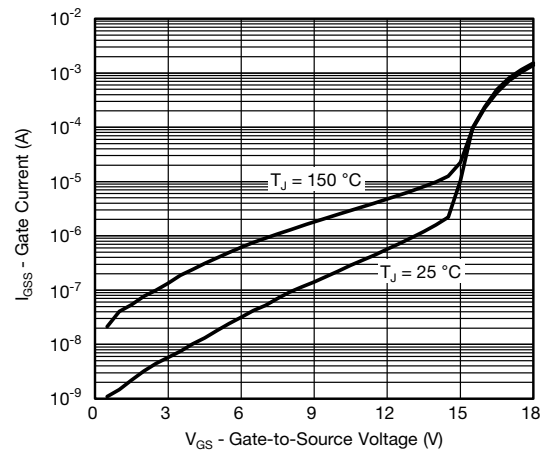

SCHOTTKY SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Forward Voltage Drop	V_F	$I_F = 0.5\text{ A}$		0.37	0.45	V
		$I_F = 0.5\text{ A}, T_J = 125\text{ }^{\circ}\text{C}$		0.31	0.37	
		$I_F = 1\text{ A}$		0.46	0.56	
		$I_F = 1\text{ A}, T_J = 125\text{ }^{\circ}\text{C}$		0.41	0.50	
Maximum Reverse Leakage Current	I_{rm}	$V_r = 30\text{ V}$		0.025	0.100	mA
		$V_r = 30\text{ V}, T_J = 85\text{ }^{\circ}\text{C}$		0.6	6	
Junction Capacitance	C_T	$V_r = 15\text{ V}$		35		pF

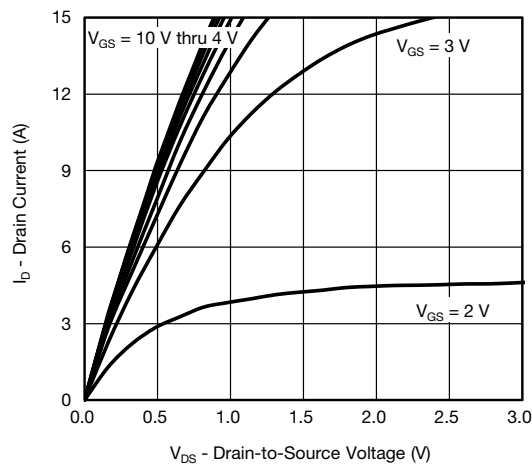
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

MOSFET TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)


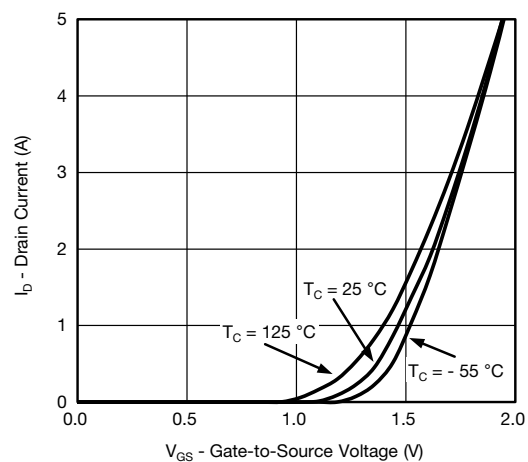
Gate-Source Voltage vs. Gate Current



Gate-Source Voltage vs. Gate Current



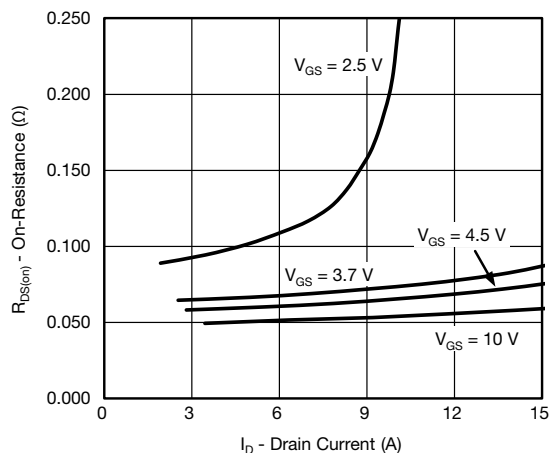
Output Characteristics



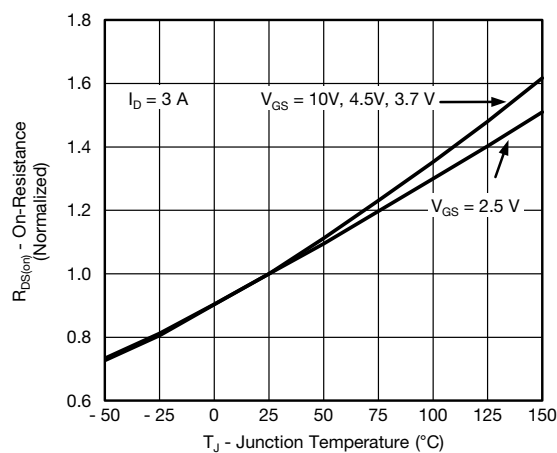
Transfer Characteristics

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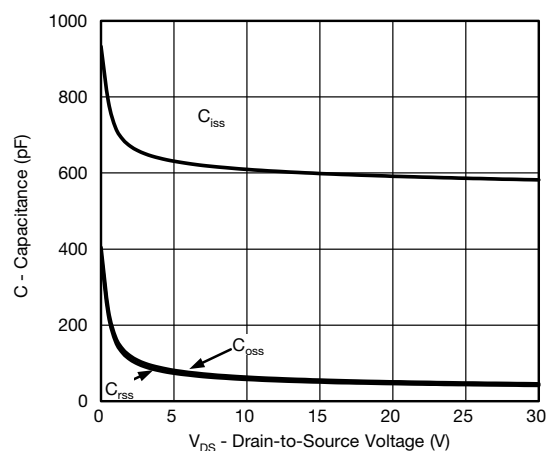
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**MOSFET TYPICAL CHARACTERISTICS** ($T_A = 25^\circ\text{C}$, unless otherwise noted)

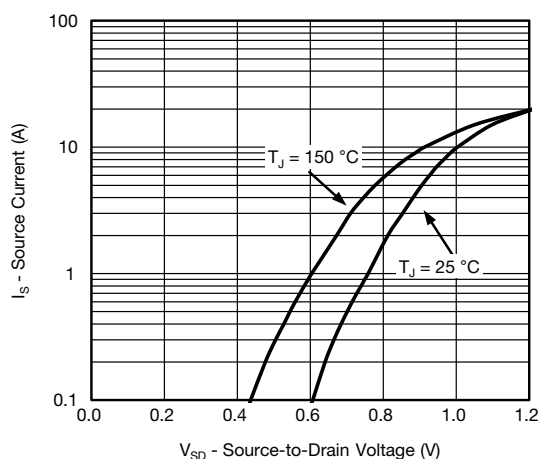
On-Resistance vs. Drain Current and Gate Voltage



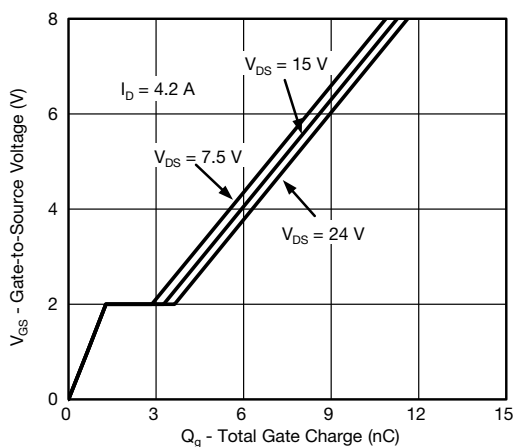
On-Resistance vs. Junction Temperature



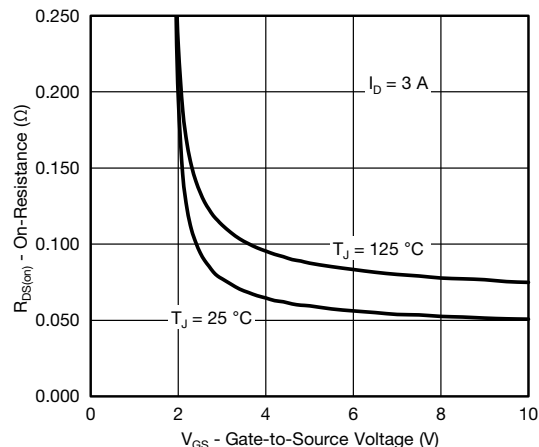
Capacitance



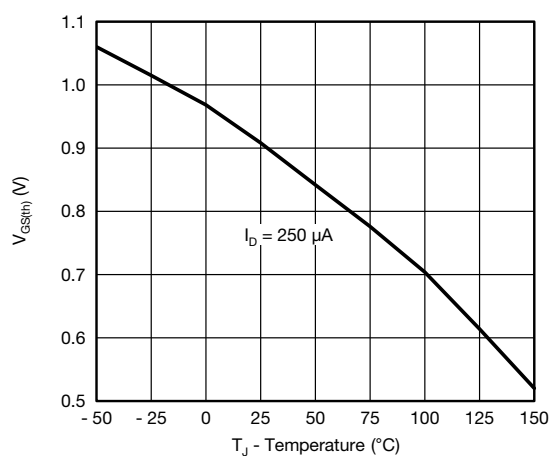
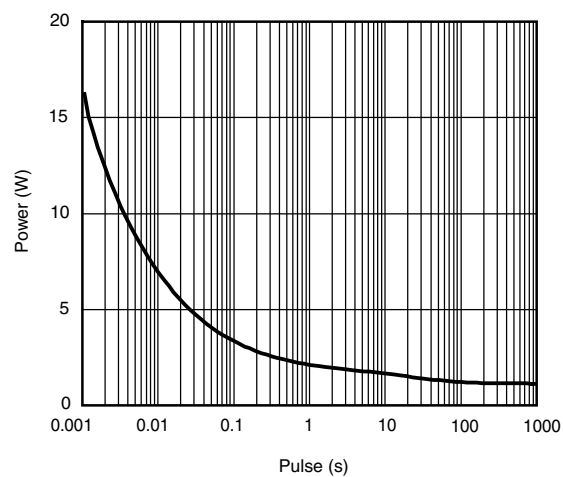
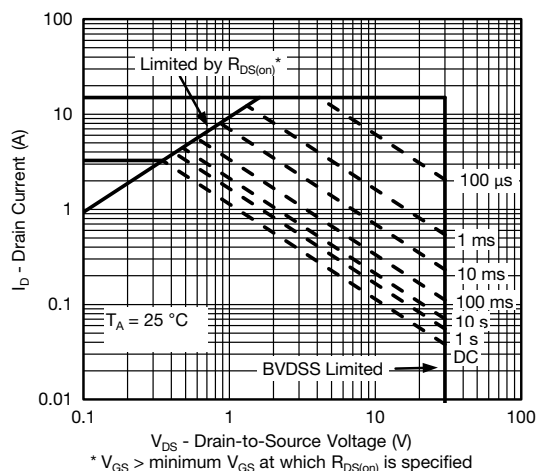
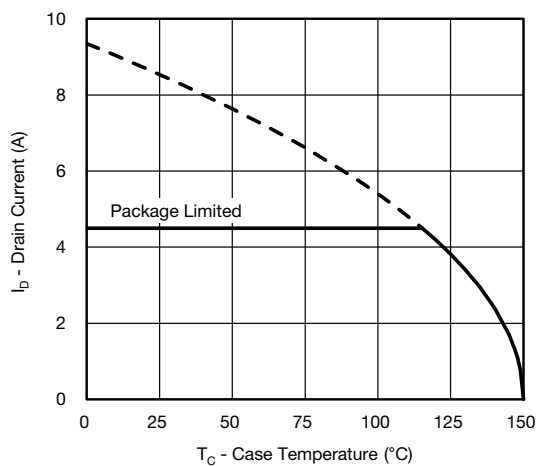
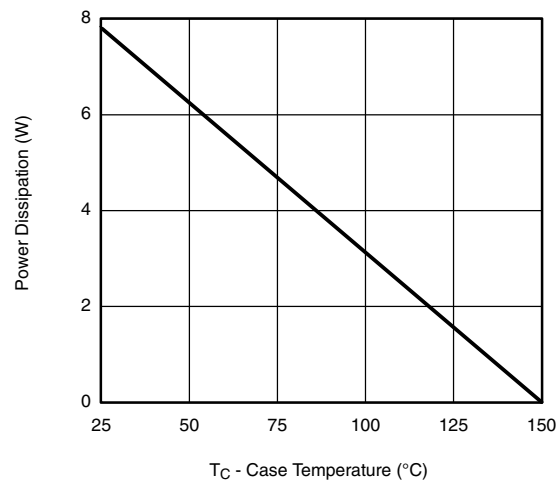
Source-Drain Diode Forward Voltage



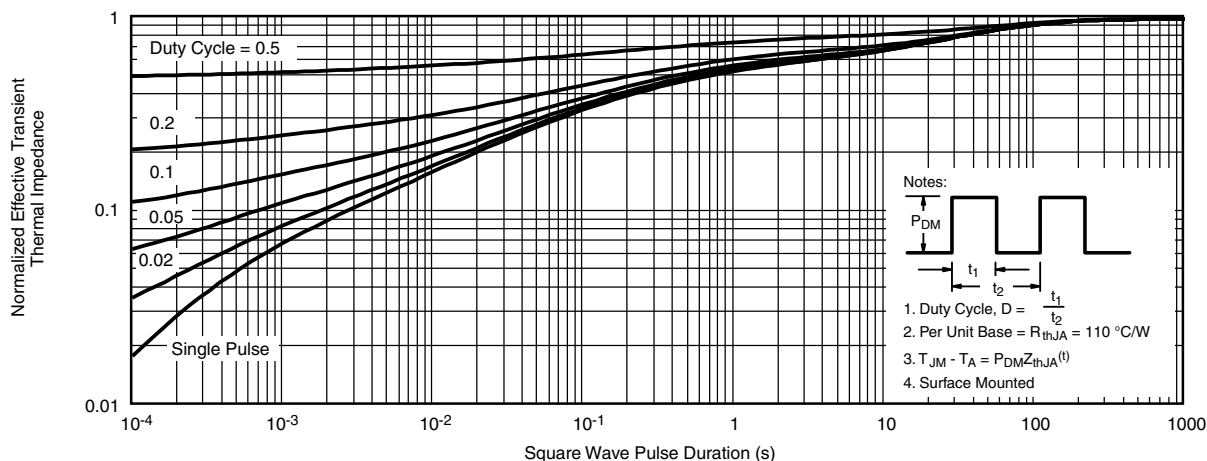
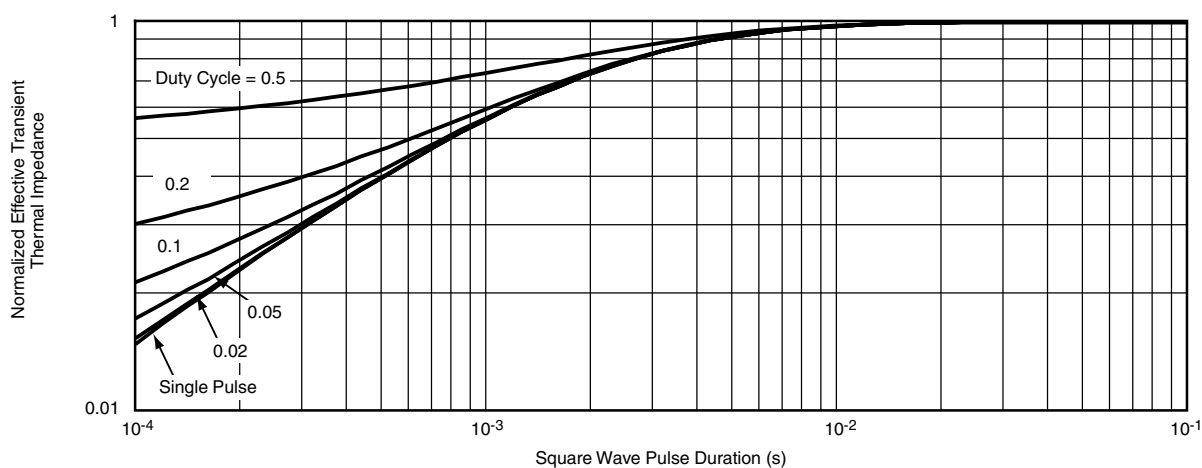
Gate Charge

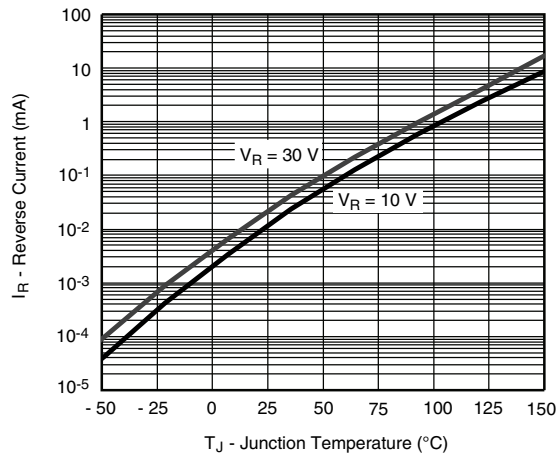
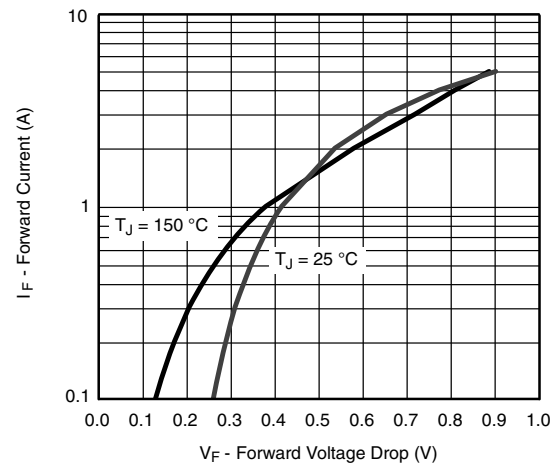
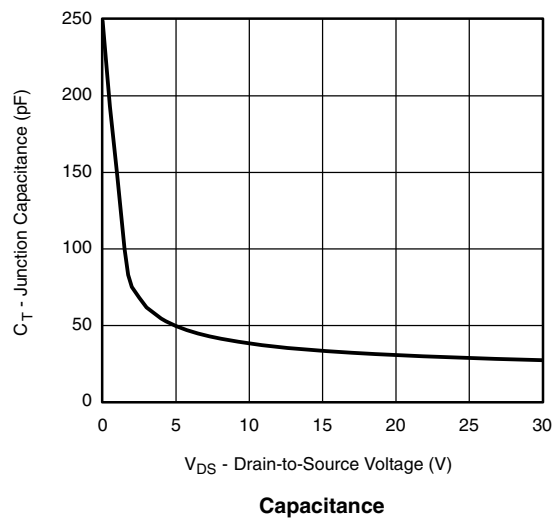


On-Resistance vs. Gate-to-Source Voltage


MOSFET TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)

Threshold Voltage

Single Pulse Power, Junction-to-Ambient

Safe Operating Area, Junction-to-Case

Current Derating*

Power Derating

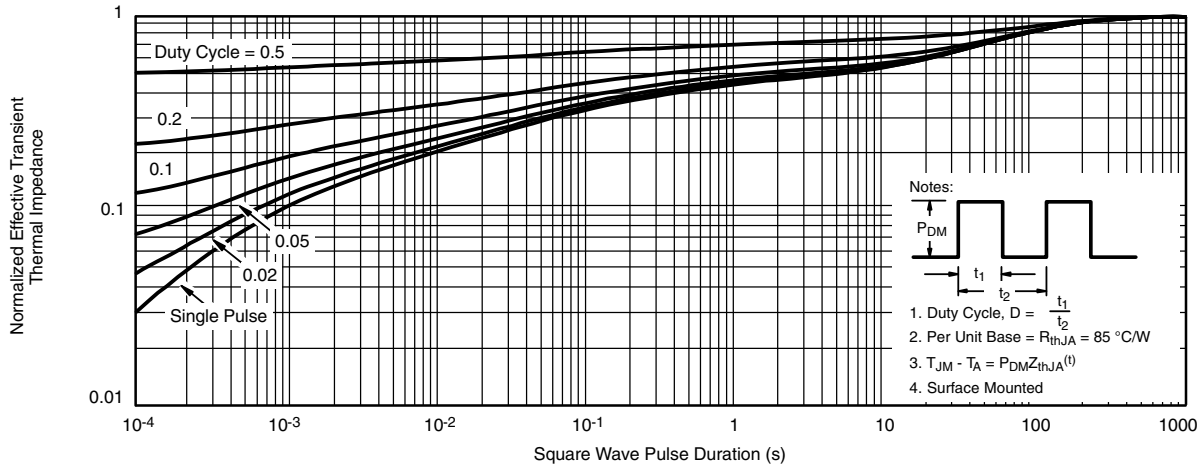
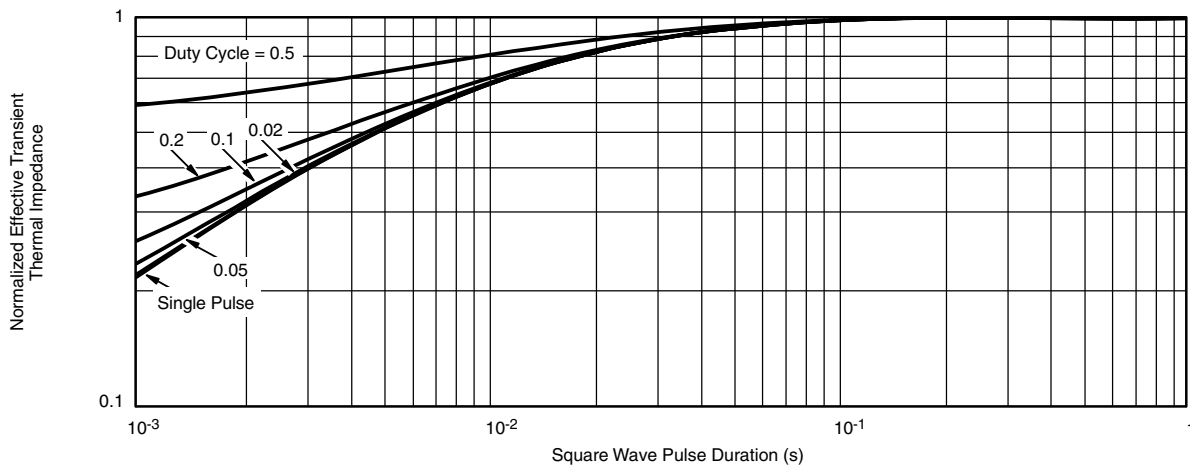
* The power dissipation P_D is based on $T_{J(max)} = 150^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

MOSFET TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Normalized Thermal Transient Impedance, Junction-to-Ambient

Normalized Thermal Transient Impedance, Junction-to-Case


SCHOTTKY TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Reverse Current vs. Junction Temperature

Forward Voltage Drop

Capacitance

SiA817EDJ

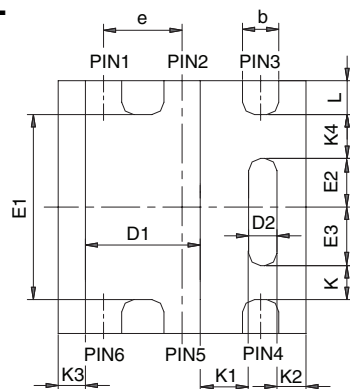
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**SCHOTTKY TYPICAL CHARACTERISTICS** ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)**Normalized Thermal Transient Impedance, Junction-to-Ambient****Normalized Thermal Transient Impedance, Junction-to-Case**

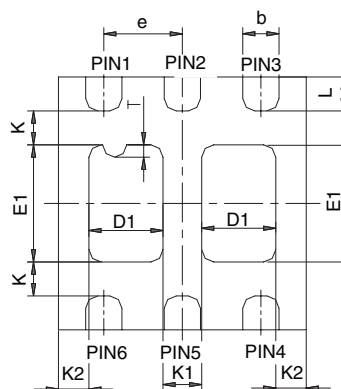
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62820.



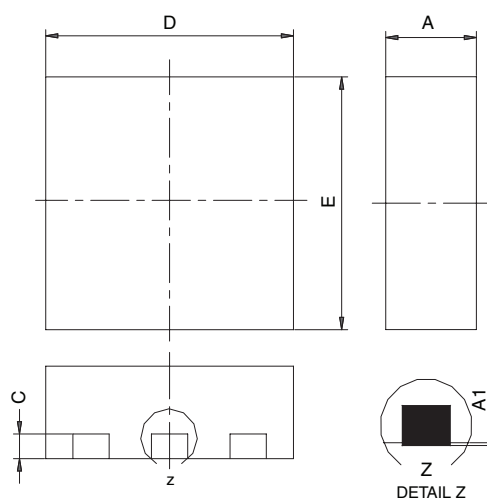
PowerPAK® SC70-6L



BACKSIDE VIEW OF SINGLE



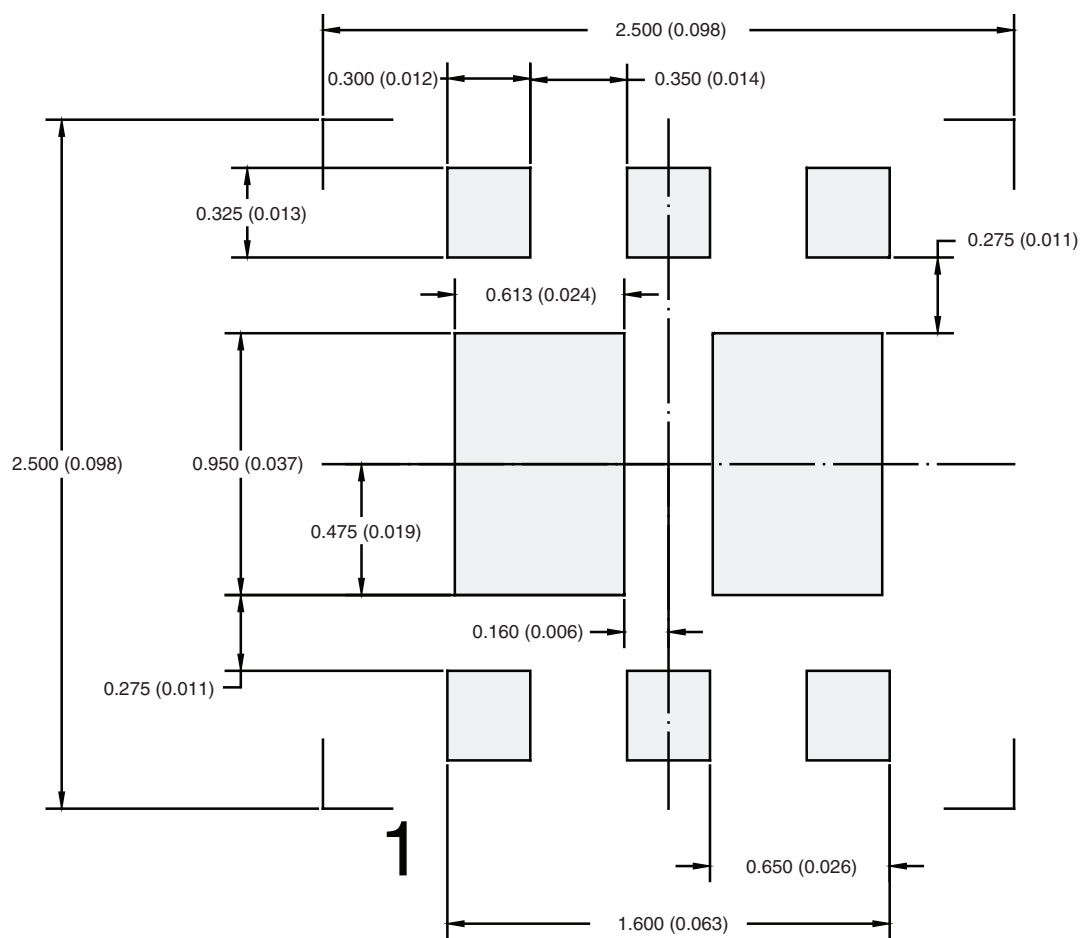
BACKSIDE VIEW OF DUAL



- Notes:
1. All dimensions are in millimeters
 2. Package outline exclusive of mold flash and metal burr
 3. Package outline inclusive of plating

DIM	SINGLE PAD						DUAL PAD					
	MILLIMETERS			INCHES			MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max
A	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015
C	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
D1	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028
D2	0.135	0.235	0.335	0.005	0.009	0.013						
E	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041
E2	0.345	0.395	0.445	0.014	0.016	0.018						
E3	0.425	0.475	0.525	0.017	0.019	0.021						
e	0.65 BSC			0.026 BSC			0.65 BSC			0.026 BSC		
K	0.275 TYP			0.011 TYP			0.275 TYP			0.011 TYP		
K1	0.400 TYP			0.016 TYP			0.320 TYP			0.013 TYP		
K2	0.240 TYP			0.009 TYP			0.252 TYP			0.010 TYP		
K3	0.225 TYP			0.009 TYP								
K4	0.355 TYP			0.014 TYP								
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015
T							0.05	0.10	0.15	0.002	0.004	0.006
ECN: C-07431 – Rev. C, 06-Aug-07												
DWG: 5934												

RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Dual



Dimensions in mm (inches)



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